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P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
- 100	0.035 at V _{GS} = - 10 V	- 39	11.7		
- 100	0.038 at V _{GS} = - 4.5 V	- 32	11.7		

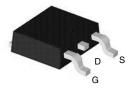
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Power Switch
- DC/DC Converters

TO-252 Pin Configuration



Top View

G

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25 \text{ °C}$, unless otherwise noted						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	- 100	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T ₁ = 150 °C)	T _C = 25 °C	1-	- 39	٨		
Continuous Drain Current (1) = 130°C)	T _C = 70 °C	I _D	- 33.1			
Pulsed Drain Current	I _{DM}	- 142	A			
Avalanche Current	I _{AS}	- 28				
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	25.7	mJ		
	T _C = 25 °C	P	88.4 ^b	W		
Maximum Power Dissipation ^a	T _A = 25 °C ^c		3.9			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)	R _{thJC}	2.2			

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).



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Parameter Symbol		Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_D = -250 \mu A$	- 100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 3.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		V _{DS} = - 100 V, V _{GS} = 0 V			- 1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 100 V, V_{GS} = 0 V, T_{J} = 125 °C			- 50		
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 150 °C			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 10 V, V_{GS} = - 10 V	- 142			А	
	D	V _{GS} = - 10 V, I _D = - 3.6 A		0.035	0.040	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.4 A		0.038	0.045		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.6 A		17		S	
Dynamic ^b	•	·			· · · · · · ·		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 50 V, f = 1 MHz		922		pF	
Output Capacitance	C _{oss}			85			
Reverse Transfer Capacitance	C _{rss}]		61			
Total Cata Charge	Qg	$V_{DS} = -50 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -3.6 \text{ A}$		28.2		nC	
Total Gate Charge ^c				19.3			
Gate-Source Charge ^c	Q _{gs}	V_{DS} = - 50 V, V_{GS} = - 4.5 V, I_{D} = - 3.6 A		5.1			
Gate-Drain Charge ^c	Q _{gd}			5.4			
Gate Resistance	Rg	f = 1 MHz	1.2	5.7	11.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			7	14		
Rise Time ^c	t _r	V_{DD} = - 50 V, R_L = 17.2 Ω		12	18	200	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 2.9 A, V_{GEN} = - 10 V, R_g = 1 Ω		33	50	ns	
Fall Time ^c	t _f			9	18		
Drain-Source Body Diode Ratings a	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	۱ _S				- 39	•	
Pulsed Current	I _{SM}	SM			-142	A	
Forward Voltage ^a	V _{SD}	I _F = - 2.9 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			50	75	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	А	
Reverse Recovery Charge	Q _{rr}	1 1		98	147	nC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

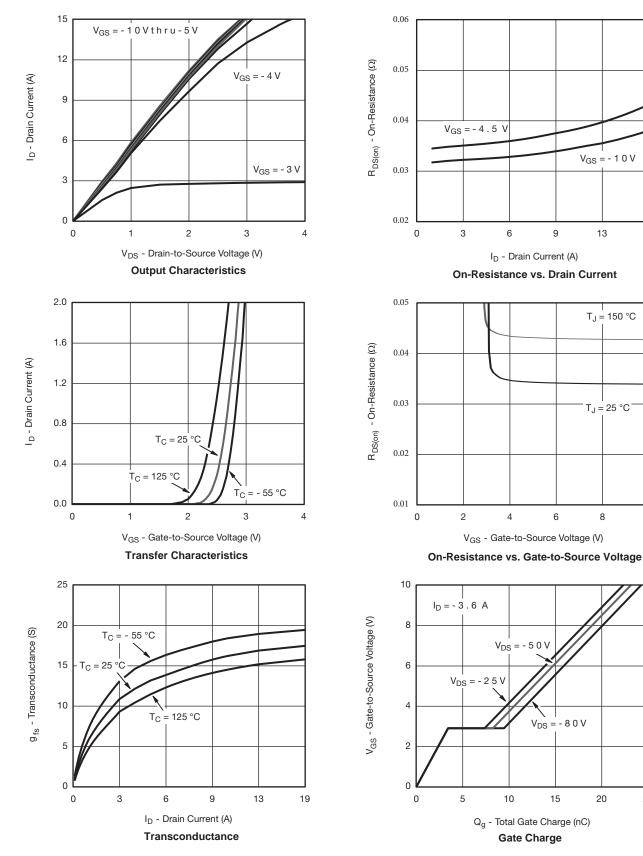


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-10V

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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100 - 1.1 - 1.4 I_S - Source Current (A) T_J = 150 °C $I_D = 250 \ \mu A$ 10 $V_{GS(th)}$ (V) - 1.7 T_J = 25 °C 1 - 2.0 0.1 - 2.3 - 50 - 25 0 25 50 75 150 0.0 0.3 0.6 0.9 1.2 100 125 V_{SD} - Source-to-Drain Voltage (V) T_J - Temperature (°C) Source-Drain Diode Forward Voltage **Threshold Voltage** 1600 - 100 V_{DS} - Drain-to-Source Voltage (V) - 106 1200 Ciss I_D = 250 μA C - Capacitance (pF) - 112 800 - 118 400 - 124 Coss 0 - 130 20 40 60 80 100 - 25 0 25 50 75 100 150 0 - 50 125 T_J - Junction Temperature (°C) V_{DS} - Drain-to-Source Voltage (V) Drain Source Breakdown vs. Junction Temperature Capacitance 2.1 40 V_{GS} 0 I_D = - 3.6 A 32 1.7 R_{DS(on)} - On-Resistance I_D - Drain Current (A) (Normalized) 24 $V_{GS} =$ 4.5 V 1.3 16 0.9 8 0.5 0 - 25 - 50 0 25 50 75 100 125 150 0 25 50 75 100 125 150 T_J - Junction Temperature (°C) T_C - Case Temperature (°C) **On-Resistance vs. Junction Temperature Current Derating**



I_{DAV} (A)

100

10

1 – 10⁻⁶

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

T_J = 25 °C

T_J = 150 °C

10⁻⁵

www.din-tek.jp 100 Limited by R_{DS(on)} 39 I_D - Drain Current (A) 100 µs 1 ms 1 10 ms 100 ms 1 s, 10 s, DC T_A = 25 °C Single Pulse 0.1 **BVDSS** Limited 0.01 10-1 0.1 1 10 100 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

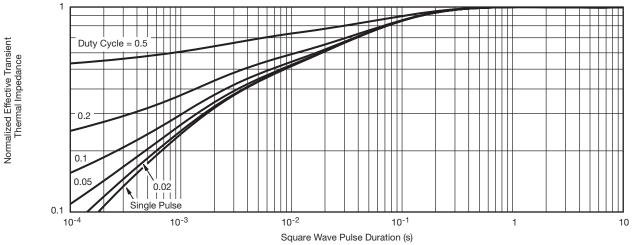
Time (s) Single Pulse Avalanche Current Capability vs. Time

10⁻³

10⁻²

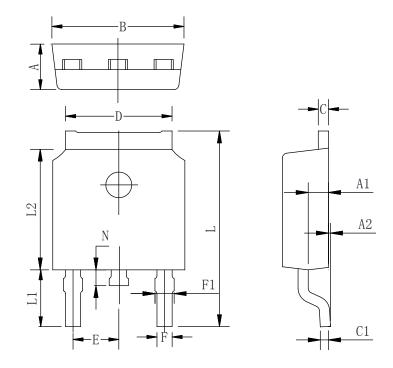
10-4

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
С	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е		2.286 TYP	
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05



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